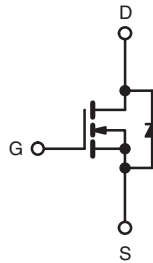
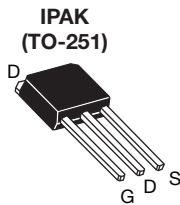


Power MOSFET

| PRODUCT SUMMARY | | |
|---------------------------|-----------------|------|
| V_{DS} (V) | 100 | |
| $R_{DS(on)}$ (Ω) | $V_{GS} = 10$ V | 0.54 |
| Q_g (Max.) (nC) | 8.3 | |
| Q_{gs} (nC) | 2.3 | |
| Q_{gd} (nC) | 3.8 | |
| Configuration | Single | |



N-Channel MOSFET

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Straight Lead
- Available in Tape and Reel
- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC



Available
RoHS*
 COMPLIANT
 HALOGEN
FREE
 Available

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

| ORDERING INFORMATION | |
|---------------------------------|---------------|
| Package | IPAK (TO-251) |
| Lead (Pb)-free and Halogen-free | SiHFU110-GE3 |
| Lead (Pb)-free | IRFU110PbF |
| | SiHFU110-E3 |
| SnPb | IRFU110 |
| | SiHFU110 |



| ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted) | | | | |
|---|------------------|----------------|------------------|------|
| PARAMETER | SYMBOL | LIMIT | UNIT | |
| Drain-Source Voltage | V_{DS} | 100 | V | |
| Gate-Source Voltage | V_{GS} | ± 20 | | |
| Continuous Drain Current | V_{GS} at 10 V | $T_C = 25$ °C | A | |
| | | $T_C = 100$ °C | | |
| Pulsed Drain Current ^a | I_{DM} | 17 | | |
| Linear Derating Factor | | 0.2 | W/°C | |
| Single Pulse Avalanche Energy ^b | E_{AS} | 75 | mJ | |
| Repetitive Avalanche Current ^a | I_{AR} | 4.3 | A | |
| Repetitive Avalanche Energy ^a | E_{AR} | 2.5 | mJ | |
| Maximum Power Dissipation | $T_C = 25$ °C | P_D | 25 | W |
| Peak Diode Recovery dV/dt^c | | dV/dt | 5.5 | V/ns |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | | - 55 to + 150 | °C |
| Soldering Recommendations (Peak Temperature) | for 10 s | | 300 ^d | |

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25$ V, starting $T_J = 25$ °C, $L = 8.1$ mH, $R_g = 25$ Ω , $I_{AS} = 4.3$ A (see fig. 12).
- $I_{SD} \leq 5.6$ A, $dI/dt \leq 75$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

| THERMAL RESISTANCE RATINGS | | | | | | |
|----------------------------------|------------|------|------|------|------|--|
| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNIT | |
| Maximum Junction-to-Ambient | R_{thJA} | - | - | 110 | °C/W | |
| Maximum Junction-to-Case (Drain) | R_{thJC} | - | - | 5.0 | | |

| SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted) | | | | | | | |
|---|---------------------|--|---|------|------|-----------|---------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | | 100 | - | - | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to 25 °C , $I_D = 1\text{ mA}$ | | - | 0.63 | - | V/°C |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | | 2.0 | - | 4.0 | V |
| Gate-Source Leakage | I_{GSS} | $V_{GS} = \pm 20\text{ V}$ | | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$ | | - | - | 25 | μA |
| | | $V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ °C}$ | | - | - | 250 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$ | $I_D = 0.90\text{ A}^b$ | - | - | 0.54 | Ω |
| Forward Transconductance | g_{fs} | $V_{DS} = 50\text{ V}, I_D = 0.90\text{ A}$ | | 1.1 | - | - | S |
| Dynamic | | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5 | | - | 180 | - | pF |
| Output Capacitance | C_{oss} | | | - | 81 | - | |
| Reverse Transfer Capacitance | C_{rss} | | | - | 15 | - | |
| Total Gate Charge | Q_g | $V_{GS} = 10\text{ V}$ | $I_D = 5.6\text{ A}, V_{DS} = 80\text{ V}$, see fig. 6 and 13 ^b | - | - | 8.3 | nC |
| Gate-Source Charge | Q_{gs} | | | - | - | 2.3 | |
| Gate-Drain Charge | Q_{gd} | | | - | - | 3.8 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 50\text{ V}, I_D = 5.6\text{ A}, R_g = 24\text{ }\Omega, R_D = 8.4\text{ }\Omega$, see fig. 10 ^b | | - | 6.9 | - | ns |
| Rise Time | t_r | | | - | 16 | - | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | - | 15 | - | |
| Fall Time | t_f | | | - | 9.4 | - | |
| Internal Drain Inductance | L_D | Between lead, 6 mm (0.25") from package and center of die contact  | | - | 4.0 | - | nH |
| Internal Source Inductance | L_S | | | - | 6.0 | - | |
| Drain-Source Body Diode Characteristics | | | | | | | |
| Continuous Source-Drain Diode Current | I_S | MOSFET symbol showing the integral reverse p - n junction diode  | | - | - | 1.5 | A |
| Pulsed Diode Forward Current ^a | I_{SM} | | | - | - | 12 | |
| Body Diode Voltage | V_{SD} | $T_J = 25\text{ °C}, I_S = 1.5\text{ A}, V_{GS} = 0\text{ V}^b$ | | - | - | 2.5 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $T_J = 25\text{ °C}, I_F = 5.6\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$ | | - | 100 | 200 | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | | - | 0.44 | 0.88 | μC |
| Forward Turn-On Time | t_{on} | Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D) | | | | | |

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

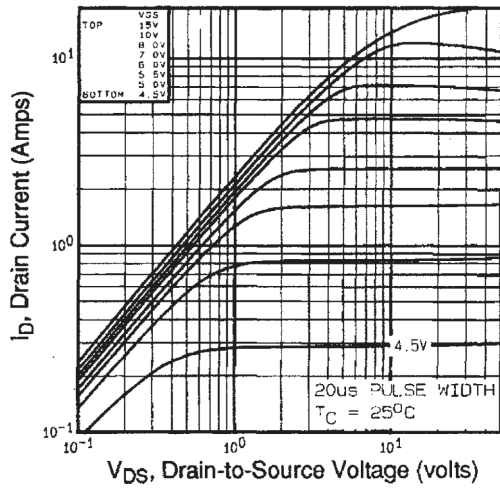


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

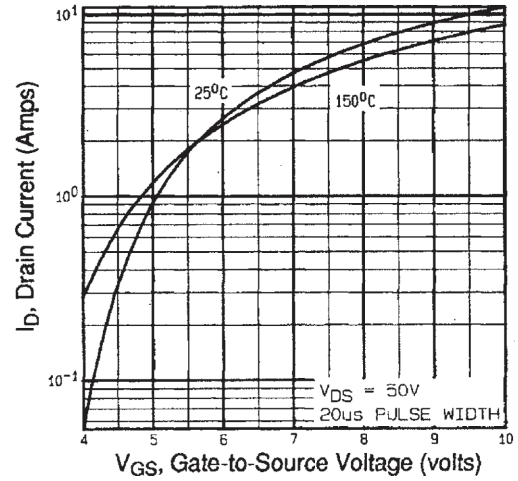


Fig. 3 - Typical Transfer Characteristics

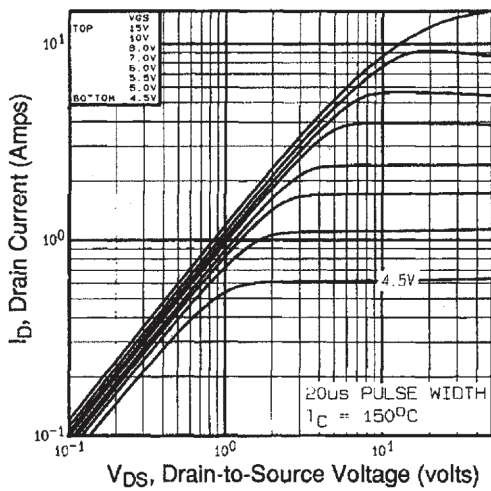


Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

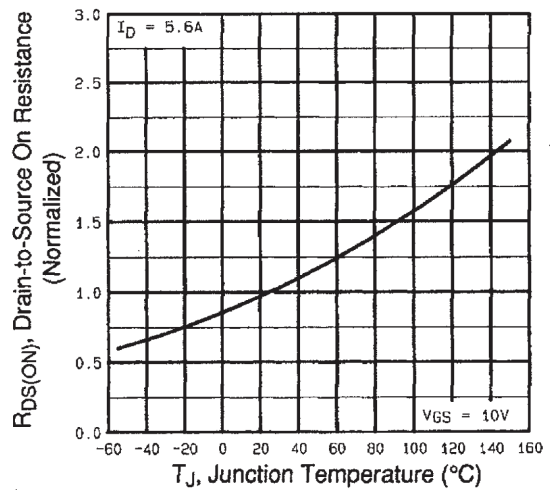


Fig. 4 - Normalized On-Resistance vs. Temperature

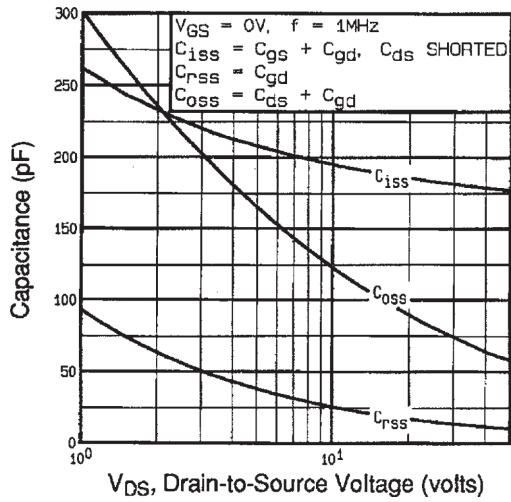


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

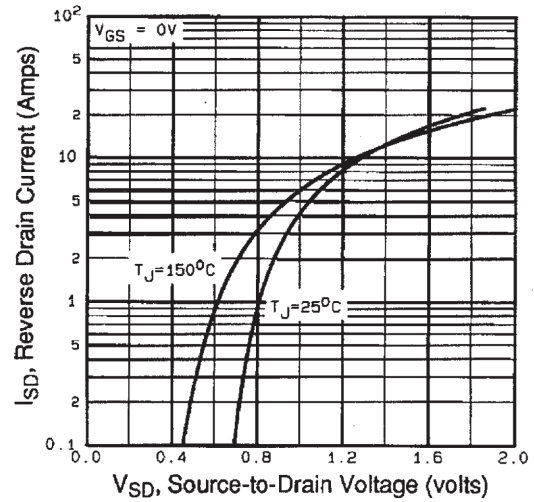


Fig. 7 - Typical Source-Drain Diode Forward Voltage

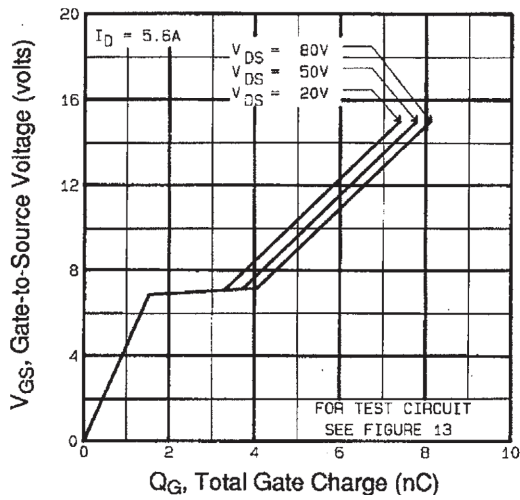


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

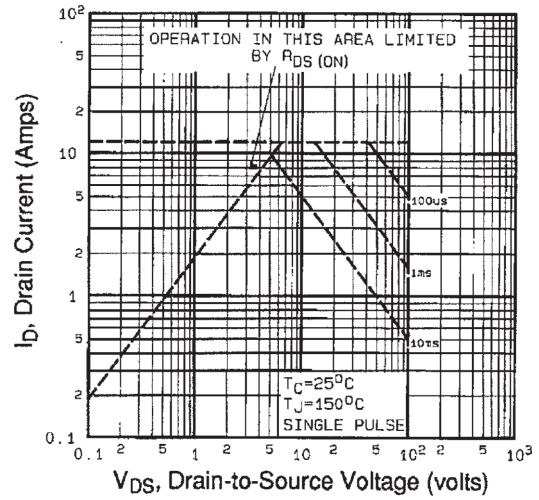


Fig. 8 - Maximum Safe Operating Area

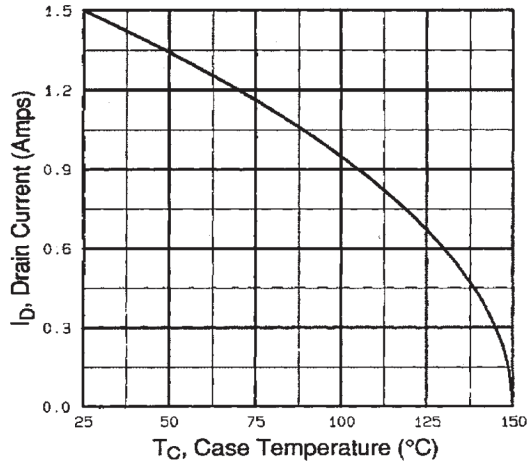


Fig. 9 - Maximum Drain Current vs. Case Temperature

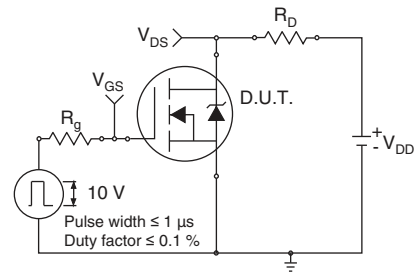


Fig. 10a - Switching Time Test Circuit

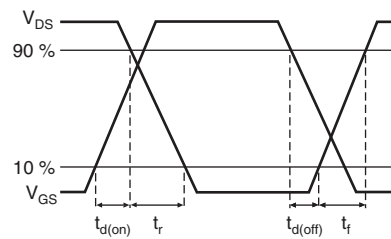


Fig. 10b - Switching Time Waveforms

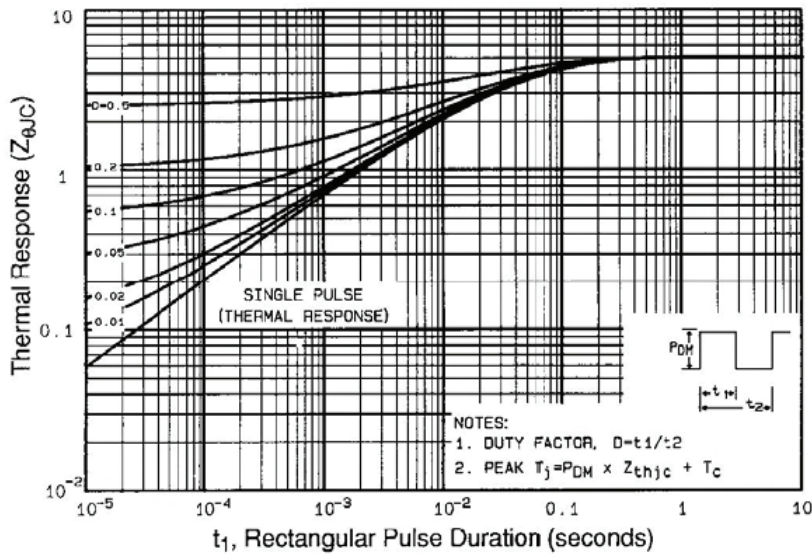


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

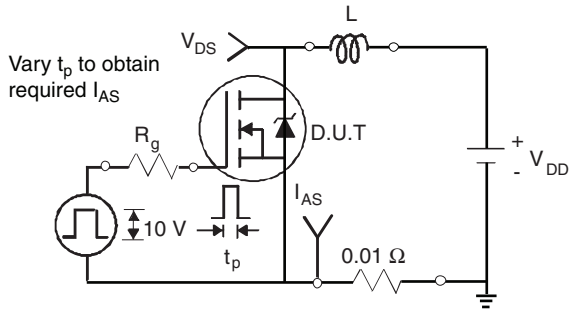


Fig. 12a - Unclamped Inductive Test Circuit

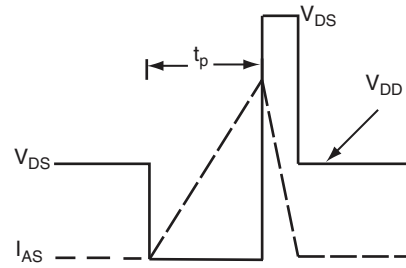


Fig. 12b - Unclamped Inductive Waveforms

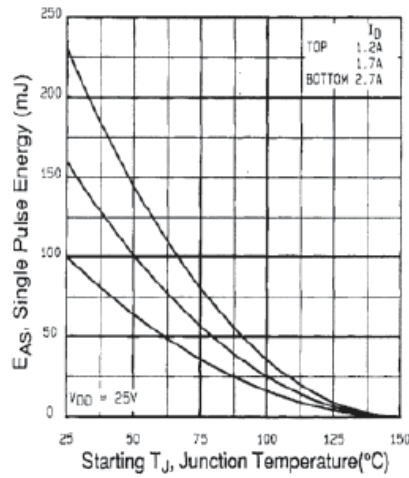


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

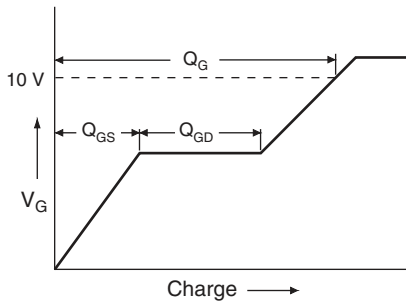


Fig. 13a - Basic Gate Charge Waveform

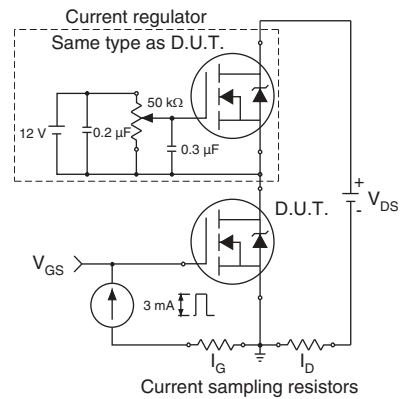
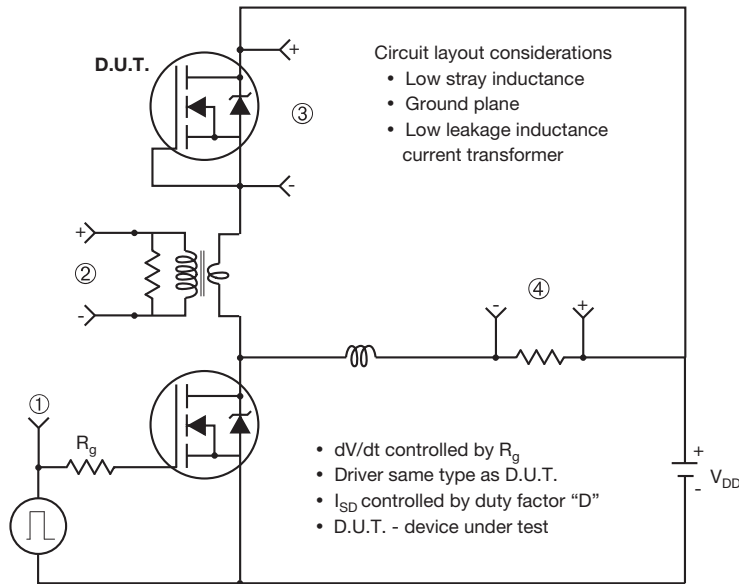


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig.14 - For N-Channel

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